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RLT1060-10G

- Infrared FP Laser Diode
- 1060 ± 10 nm, 10 mW CW
- Single Transverse Mode
- 9 mm TO package, flat window
- Built-in Monitor PD

Description

RLT1060-10G is a infrared FP Laser Diode emitting at typical 1060 nm with rated output power of 10 mW CW at room temperature. The 9 mm TO package includes a cap and flat window, and contains a built in **monitor PD**.

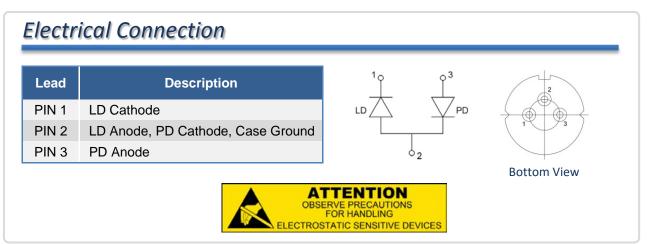
Maximum Ratings

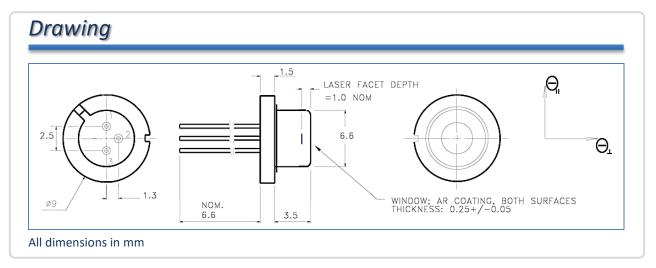
Parameter	Symbol	Va	Unit	
		Min.	Max.	Unit
Optical Output Power	Po			mW
Operating Temperature	T _{CASE}	-40	+50	°C
Storage Temperature	T _{STG}	-40	80	°C
Soldering Temperature	T _{SOLD}		180	°C

Specifications (at 25°C)

Parameter	Symbol	Values			Unit
	Symbol	Min.	Тур.	Max.	Unit
Central Wavelength	$\lambda_{\rm C}$	1050	1060	1070	nm
Spectral Width (FWHM)	Δλ	-	-	5	nm
Optical Output Power	Po	-	10	-	mW
Emitting Area	W x H		5 x 1		μm
Threshold Current	I _{TH}	-	-	30	mA
Forward Current	I _{OP}	-	-	50	mA
Forward Voltage	U _{OP}	-	1.3	1.5	V
Beam Divergence	θII	5	7	9	deg.
Beam Divergence	θ⊤	35	40	45	deg.
Mode Structure			SM		-
Monitor Current	I _M	1	-	1000	μA

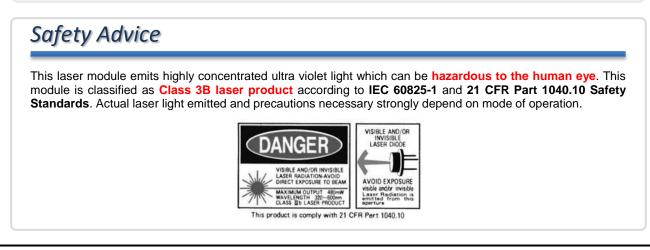






Mounting Instruction

In order to maintain lifetime and stability of the laser diode it is essential to provide efficient heat management. Heat dissipation is possible through the base plate only. For long time stable operation proper contact between laser diode base plate and heat sink is mandatory.



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